

Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6	((("6504123") or ("6594611") or ("6529793"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 03:42
L2	2	("5431772").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 03:43
L3	17	((("5431772") or ("5500532") or ("5761115") or ("5896312") or ("5914893") or ("6084796") or ("6388324") or ("6418049") or ("6469364") or ("6487106"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 03:53
L4	2	"09941544"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 03:54
L5	2	"20030047765"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 03:55
L6	2	"20040038480"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 03:58
L7	3	("6818481").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 04:34
L8	527	memory and (bit adj line) and substrate and transistor and ((variable adj state) or (resistance with variable))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:37

L9	128	8 and (first with level) and (second with level) and (third with level)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:37
L10	86	9 and above and below	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:38
L11	82	10 and (resistance with variable)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:48
L12	12	11 and (variable with state)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:38
L13	8	11 and chalcogenide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:50
L14	16	8 and moore\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:50
L15	515	8 and (resistance with variable)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:54
L16	285	15 and (variable adj resistance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:55

L17	267	16 and (bit adj line) and (word adj line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:55
L18	267	17 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:56
L19	236	18 and insulat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:56
L20	43	19 and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:56
L21	307	8 and "365"/\$7.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:57
L22	31	20 and 21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:58
L23	1	(memory and (bit adj line) and (first with level) and substrate and (second with level) and above and below and signal and (variable adj state) and (third with level) and switch\$3).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 04:59